

| 1 | 1. An inita Red (IR) sensing device comprising: | | | | | |
|--------------|--|--|--|--|--|--|
| 2 | an IR sensing element for detecting IR radiation, wherein the IR sensing | | | | | |
| 3 | element includes a plurality of thermopile elements with connections to both ends and to a | | | | | |
| 4 | center point of the sensing element; | | | | | |
| 5 | a processing circuit having two inputs coupled to the IR sensing element and | | | | | |
| 6 | configured to receive and analyze the electrical signals generated by the IR sensing element; | | | | | |
| 7 | protection circuitry coupled to the two inputs and a first potential; and | | | | | |
| .i. 8 | an electrically conducting housing connected to the first potential, | | | | | |
| 8 9 10 | wherein the processor connects the center point of the sensing element to the | | | | | |
| 10 | first potential and the ends of the sensing element to the two inputs, wherein the processing | | | | | |
| 11 | circuit analyzes the signals from the ends of the sensing element as a differential pair of | | | | | |
| 12 | signals relative to the first potential. | | | | | |
| . 1 | 2. The device of claim 1, wherein the processing circuit is embodied as | | | | | |
| 2 | an integrated circuit. | | | | | |
| 1 | 3. The device of claim 2, wherein the first potential is connected to the | | | | | |
| 2 | 3. The device of claim 2, wherein the first potential is connected to the substrate of the integrated circuit. | | | | | |
| 2 | substrate of the integrated eneurt. | | | | | |
| 1 | 4. The device of claim 1, wherein the processing circuit includes | | | | | |
| 2 | configuration circuitry. | | | | | |
| 1 | 5. The device of claim 1, wherein the processing circuit includes | | | | | |
| 2 | calibration circuitry. | | | | | |
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| 1 | 6. The device of claim 4 or 5, wherein the processing circuit includes a | | | | | |
| 2 | non-volatile memory for storing calibration or configuration data. | | | | | |
| 1 | 7. The device of claim 6, wherein the non-volatile memory is | | | | | |
| 2 | programmed after manufacture. | | | | | |
| 1 | 8. The device of claim 6, wherein the non-volatile memory is | | | | | |
| 2 | programmed after the device has been installed in its operating location. | | | | | |
| 1 | 9. An Infra Red (IR) sensing device comprising: | | | | | |

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| | 3 | one of | the first ar | nd se | cor |
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2

| an IR sensing element for detecting IR radiation, wherein the IR sensing | | | | |
|---|--|--|--|--|
| element includes a plurality of serially connected thermopile elements; | | | | |
| a processing circuit configured to receive and process the electrical signals | | | | |
| generated by the thermopile elements, the processing circuit having first and second inputs | | | | |
| coupled to the two ends of the series of thermopile elements and a third input coupled to a | | | | |
| center point of the series of thermopile elements and to a first potential; and | | | | |
| protection circuitry coupled to the two inputs and the first potential; | | | | |
| wherein the processing circuit processes the signals at the first and second | | | | |
| inputs as a differential pair of signals relative to the first potential so as to produce a | | | | |
| temperature readout signal. | | | | |
| | | | | |

- 10. The sensing device of claim 9, further comprising an electrically onducting housing connected to the first potential.
- 11. The sensing device of claim 9, wherein the protection circuitry includes a pair of diode structures, each diode structure coupled to the first potential and to one of the first and second inputs.
- 12. The sensing device of claim 9, wherein the processing circuit is implemented on a first integrated circuit.
- 1 13. The sensing device of claim 12, wherein the sensing element is 2 implemented on a second integrated circuit.
- 1 14. The sensing device of claim 12, wherein the protection circuitry is 2 implemented on the first integrated circuit.
- 1 15. The sensing device of claim 9, further comprising a conductive 2 housing connected to the first potential.